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(54) **SPIN TRANSFER TORQUE TUNNELING MAGNETORESISTIVE DEVICE HAVING A LAMINATED FREE LAYER WITH PERPENDICULAR MAGNETIC ANISOTROPY**

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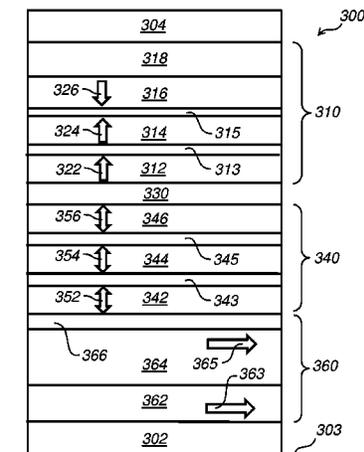
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(57) **ABSTRACT**

A spin transfer torque magnetic junction includes a magnetic reference layer structure with magnetic anisotropy perpendicular to a substrate plane. A laminated magnetic free layer comprises at least three sublayers (e.g. sub-layers of CoFeB, CoPt, FePt, or CoPd) having magnetic anisotropy perpendicular to the substrate plane. Each such sublayer is separated from an adjacent one by a dusting layer (e.g. tantalum). An insulative barrier layer (e.g. MgO) is disposed between the laminated free layer and the magnetic reference layer structure. The spin transfer torque magnetic junction includes conductive base and top electrodes, and a current polarizing structure that has magnetic anisotropy parallel to the substrate plane. In certain embodiments, the current polarizing structure may also include a non-magnetic spacer layer (e.g. MgO, copper, etc).

23 Claims, 3 Drawing Sheets



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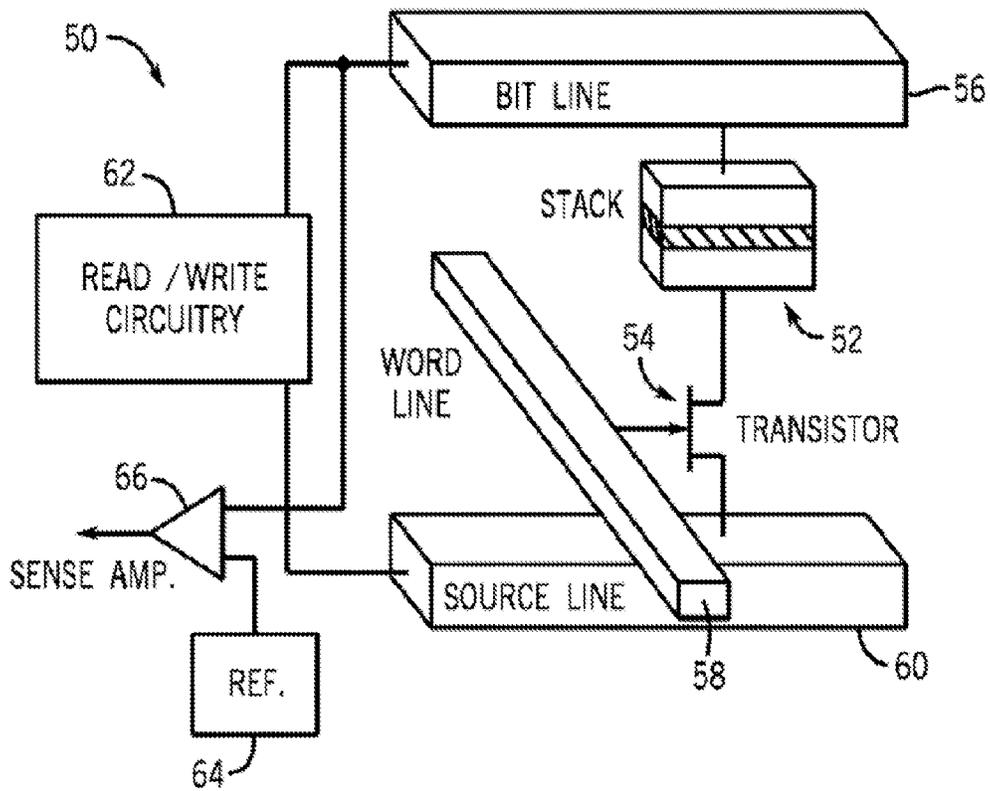


FIG. 1
(PRIOR ART)

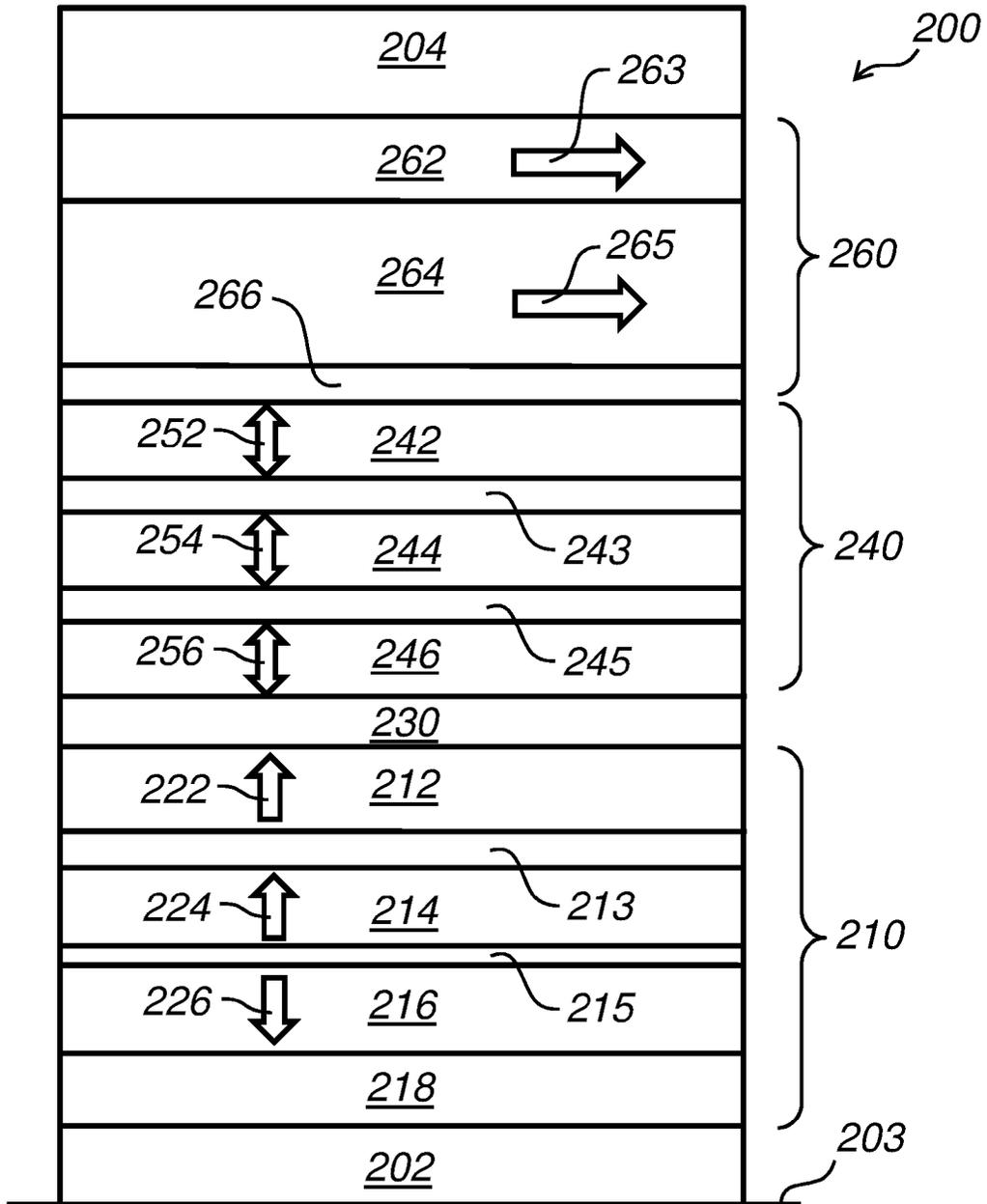


FIG. 2

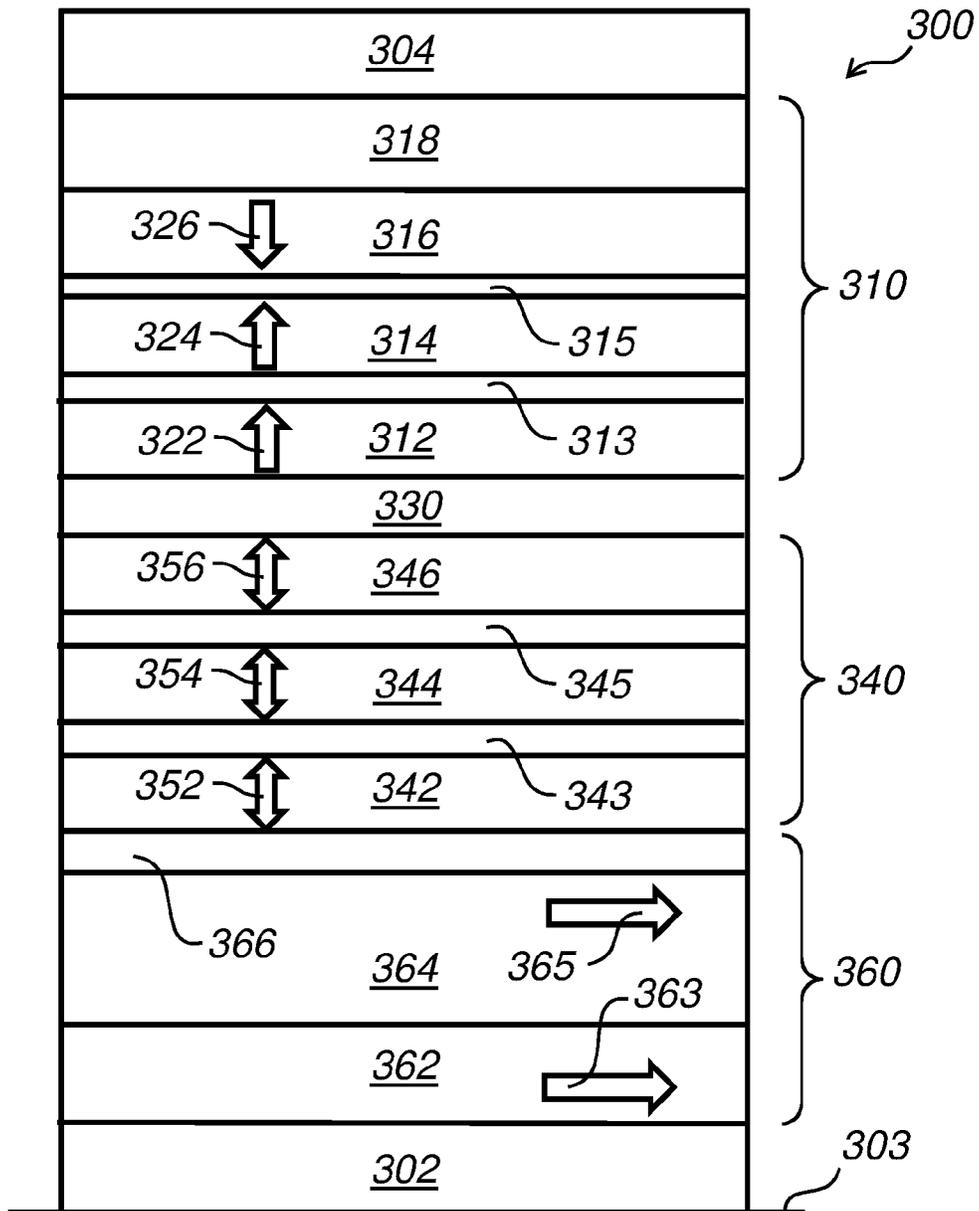


FIG. 3

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**SPIN TRANSFER TORQUE TUNNELING
MAGNETORESISTIVE DEVICE HAVING A
LAMINATED FREE LAYER WITH
PERPENDICULAR MAGNETIC
ANISOTROPY**

RELATED APPLICATION

This application is a continuation of U.S. patent application Ser. No. 14/563,721 to Shaoping Li, entitled "Spin Transfer Torque Tunneling Magnetoresistive Device Having a Laminated Free Layer with Perpendicular Magnetic Anisotropy," filed 2014 Dec. 8, pending.

BACKGROUND

Information storage devices are manufactured in high volume and widely used to store and/or retrieve data in computers and other consumer electronics devices. Information storage devices may be classified as volatile or non-volatile, depending upon whether their memory content is maintained when the information storage device is not powered. Examples of non-volatile information storage devices include magnetic hard disk drives and magnetic random access memory (MRAM) devices, either of which may utilize a magnetoresistive tunnel junction (MTJ) as part of information storage or retrieval operations. Specifically, whereas volatile random access memory (RAM) devices typically store data as electric charge, MRAM devices may store data in MTJs that maintain memory content even when the memory device is not powered.

Generally, each MTJ includes a reference layer that has a magnetic orientation that is pinned or fixed, and a free layer having a magnetic orientation that can be changed by an external magnetic field (e.g. from an adjacent disk or generated by a programming current). The MTJ is in a low resistance state when the free layer magnetic orientation is parallel to that of the reference layer, and in a high resistance state when the free layer magnetic orientation is anti-parallel to that of the reference layer. If the external magnetic field and/or programming current required to switch a desired MTJ between high and low resistance states (with acceptable switching speed) is too great, or if the MTJs are arranged too closely together, then one or more adjacent MTJs may undesirably be affected or inadvertently switched.

There have been many patented variations and improvements to MTJs in recent years, some of which help mitigate the foregoing problem to allow for more reliable operation when the MTJs are arranged in close proximity to each other. For example, a spin transfer torque magnetic random access memory (STT-MRAM) has been investigated, in which each MTJ is switched (i.e. "programmed") by an application of spin polarized current through the MTJ. The STT-MRAM promises significant advantages over magnetic-field-switched MRAM, which has been recently commercialized. For example, STT-MRAM can be scaled to a smaller size while maintaining the programmability of individual MTJs (without inadvertently and undesirably affecting the programming of adjacent MTJs). Moreover, STT-MRAM can be programmed with lesser programming currents, which reduces power consumption and associated requirements for heat dissipation.

However, one of the challenges for implementing STT-MRAM is minimizing the programming current required to quickly switch the magnetic orientation of the free layer in the MTJ, while maintaining high thermal stability of the

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recorded data. Reduced programming current may enable the use of smaller memory cell transistors, which can substantially reduce the overall size of the incorporating memory device. A reduced programming current requirement also corresponds to reduced voltages across the MTJs during writing and sensing, which may decrease the probability of tunneling barrier degradation and breakdown, and thereby improve the endurance and reliability of the incorporating memory device.

Hence, there is an ongoing need in the art for an improved MTJ that can quickly and reliably switch with acceptable thermal stability using a reduced programming current, and that is suitable for high volume manufacture and widespread durable use in reduced-scale data storage devices.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a schematic representation of a conventional MRAM cell that is capable of being improved by incorporating a spin transfer torque MTJ according to an embodiment of the present invention.

FIG. 2 is a cross-sectional diagram of a spin transfer torque MTJ according to certain embodiments of the present invention.

FIG. 3 is a cross-sectional diagram of a spin transfer torque MTJ according to certain alternative embodiments of the present invention.

DESCRIPTION OF THE PREFERRED
EMBODIMENTS

FIG. 1 is a schematic representation of a conventional MRAM cell 50 that is capable of operation with a conventional spin transfer torque MTJ, or being improved by incorporating a spin transfer torque MTJ according to an embodiment of the present invention.

Now referring to FIG. 1, the MRAM cell 50 includes a MTJ stack 52, an access transistor 54, a bit line 56, a word line 58, a source line 60, read/write circuitry 62, a bit line reference 64, and a sense amplifier 66. The MRAM cell 50 may be incorporated in an array of memory cells having a number of rows and columns. The MTJ stack 52 may optionally include a conventional spin transfer torque MTJ, or a spin transfer torque MTJ according to an embodiment of the present invention (described herein with specific reference to FIGS. 2 and 3).

When the MRAM cell 50 is selected to be programmed (in part by selective operation of the transistor 54 by word line 58), the read/write circuitry 62 applies a programming current through the MTJ stack 52 via the bit line 56, the source line 60, and the transistor 54. For example, the read/write circuitry 62 may apply a write voltage between the bit line 56 and the source line 60, with the polarity of such write voltage determining the remnant magnetization of the free layer in the MTJ stack 52. Specifically, the MTJ stack 52 may operate on a spin transfer torque principle, in which case electrons of the programming current become spin-polarized as the electrons pass through a spin filter layer of the MTJ stack 52. In that case, spin-polarized electrons of the programming current may exert a torque on the free layer of the MTJ stack 52, which can switch the polarity of the free layer during the writing operation.

To read the MRAM cell 50, a sensing current is used to detect the resistance state of the MTJ stack 52, with the sensing current being less than the programming current (so that sensing does not switch the free layer polarity in the MTJ stack 52). The read/write circuitry 62 may apply the

sensing current to the MTJ stack **52** via the bit line **56**, the source line **60**, and the transistor **54**. The programmed state of the MRAM cell **50** is sensed according to the resistance across the MTJ stack **52**, which may be determined by the voltage difference between the bit line **56** and the source line **60**. The voltage difference may optionally be compared to a reference **64** by a sense amplifier **66**.

FIG. 2 is a cross-sectional diagram of a spin transfer torque MTJ **200** according to certain embodiments of the present invention. The spin transfer torque MTJ **200** includes an electrically conductive base electrode layer **202** defining a substrate plane **203**. In certain embodiments, the spin transfer torque MTJ **200** may be fabricated on an electrically conductive substrate, with a remaining portion of the electrically conductive substrate serving as the electrically conductive base electrode layer **202**. In certain alternative embodiments, the electrically conductive base electrode layer **202** may be fabricated as a metal layer (e.g. NiCr) deposited on a substrate (non-conductive, semi-conductive, or electrically conductive) that might be partially or wholly removed (e.g. by a conventional etching process).

In the embodiment of FIG. 2, a magnetic reference layer structure **210** is disposed on the base electrode layer **202**. The magnetic reference layer structure **210** may include various sub-layers. For example, the magnetic reference layer structure **210** may include a pinned layer **212**, for example comprising CoFeB. The magnetic reference layer structure **210** may also include a pair of antiferromagnetically coupled pinning layers **214**, **216** separated by a thin non-magnetic dusting layer **215** (e.g. ruthenium). The magnetic reference layer structure **210** may optionally further include an outer layer **218** (optionally comprising an alloy of manganese, such as PtMn, IrMn, NiMn, FeMn), that is disposed adjacent to the base electrode layer **202**.

In FIG. 2, the arrow **222** depicts a remnant magnetic field direction in the pinned layer **212**, which corresponds to a magnetic anisotropy in the pinned layer **212** that is perpendicular to the substrate plane **203**. The arrows **224**, **226** depict the remnant magnetic field directions in the pinning layers **214**, **216**, respectively, each corresponding to a magnetic anisotropy that is perpendicular to the substrate plane **203**. Note that the terms “perpendicular” and “parallel,” as used herein do not require perfect perpendicularity or perfect parallelism, but rather approximate perpendicularity or approximate parallelism, respectively (e.g. within $\pm 10^\circ$ of the desired orientation).

In the embodiment of FIG. 2, the primary function of the reference layer structure **210** is to maintain the magnetic orientation **222** of the pinned layer **212** in a fixed (i.e. “pinned”) orientation, despite magnetic torques that may be applied to the pinned layer **212** by spin polarized electrical currents passing through the spin transfer torque MTJ **200** for programming or sensing, and regardless of external magnetic fields that the spin transfer torque MTJ **200** might experience from its environment. The pinned layer **212** may be separated from the antiferromagnetically coupled pinning layers **214**, **216**, by a thin non-magnetic metallic layer **213** (e.g. tantalum).

In the embodiment of FIG. 2, an insulative barrier layer **230** is disposed on the laminated magnetic reference layer structure **210**, so that the pinned layer **212** is disposed adjacent to the insulative barrier layer **230**. In certain embodiments, the insulative barrier layer **230** may preferably comprise MgO having a thickness in the range of 8 Angstroms to 20 Angstroms, which in certain embodiments may provide a resistance area product (“RA”) in the range 1 to 6 $\Omega\text{-}\mu\text{m}^2$.

In the embodiment of FIG. 2, a laminated magnetic free layer **240** is disposed on the insulative barrier layer **230**. In certain embodiments, the laminated magnetic free layer **240** may include at least three sublayers **242**, **244**, **246**, each one being separated from an adjacent one by a non-magnetic metallic dusting layer. For example, in the embodiment of FIG. 2, the sublayer **242** is separated from the sublayer **244** by the non-magnetic metallic dusting layer **243**, and the sublayer **244** is separated from the sublayer **246** by the non-magnetic metallic dusting layer **245**. In the embodiment of FIG. 2, each of the non-magnetic metallic dusting layers **243**, **245** may preferably be a tantalum dusting layer having a thickness in the range of 1 Angstroms to 7 Angstroms.

In the embodiment of FIG. 2, each of the sub-layers **242** and **246** of the laminated magnetic free layer **240** may preferably be a CoFeB sublayer having a thickness in the range of 6 Angstroms to 16 Angstroms. In certain embodiments, the sublayer **244** of the laminated magnetic free layer **240** may also be a CoFeB sublayer having a thickness in the range of 6 Angstroms to 16 Angstroms. In certain embodiments, the laminated magnetic free layer **240** preferably does not include more than four such CoFeB sublayers, each separated from an adjacent one by a tantalum dusting layer. However, in certain alternative embodiments, the sublayer **244** of the laminated magnetic free layer **240** may preferably comprise CoPt, FePt, or CoPd, and have a thickness in the range of 10 Angstroms to 30 Angstroms.

In the embodiment of FIG. 2, each of the arrows **252**, **254**, **256** depicts a remnant magnetic field direction in a corresponding sublayer **242**, **244**, **246** of the laminated magnetic free layer **240**, respectively. The arrows **252**, **254**, **256** are shown as double-headed arrows as an indication that the laminated free layer **240** is intended to have a magnetization that is programmable (by the passage of a polarized current) to be aligned with, or counter-aligned against, the magnetic orientation **222** of the pinned layer **212**. The arrows **252**, **254**, **256** are also drawn so as to indicate that the magnetic anisotropy of each of the sublayers **242**, **244**, **246** of the laminated magnetic free layer **240** is preferably oriented perpendicular to the substrate plane **203**.

The presently disclosed structure and composition of the laminated free layer **240** of the embodiment of FIG. 2, and its anisotropy perpendicular to the substrate plane **203**, may beneficially reduce the programming current required to change the magnetic orientation of the laminated free layer **240**. By contrast, the required programming current may be undesirably higher if the sublayers **242**, **244**, **246** of the laminated free layer **240** instead comprised FePt and/or had anisotropy parallel to the substrate plane **203**. Moreover, the presently disclosed structure and composition of the laminated free layer **240** of the embodiment of FIG. 2 may allow deposition at lower temperature, simplifying the manufacturing process and reducing the risk of thermal degradation to the fabricated spin transfer torque MTJ **200** and its tunneling magneto resistive (TMR) performance.

In the embodiment of FIG. 2, a current polarizing structure **260** is disposed on the laminated magnetic free layer **240**. The current polarizing structure **260** may include a CoFeB polarizing layer **264** having a thickness greater than 20 Angstroms, and may optionally include a CoPd layer **262**. In certain embodiments, the current polarizing structure **260** is preferably spaced from the laminated magnetic free layer **240** by a MgO spacer layer **266** that is adjacent to the laminated magnetic free layer **240**. In such embodiments, the MgO spacer layer **266** preferably has a thickness in the range of 2 to 8 Angstroms, which may provide a resistance

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area product (“RA”) in the range 0.2 to 0.8 $\Omega\cdot\mu\text{m}^2$ —preferably substantially less than that of the insulative barrier layer 230.

In the embodiment of FIG. 2, each of the arrows 263, 265 depicts a remnant magnetic field direction in the CoPd layer 262 and the CoFeB polarizing layer 264, respectively. As depicted by the arrows 263, 265, the CoPd layer 262 and the CoFeB polarizing layer 264 have magnetic anisotropy that is parallel to the substrate plane 203.

In the embodiment of FIG. 2, the spin transfer torque MTJ 200 further includes an electrically conductive top electrode layer 204 that is disposed on the current polarizing structure 260, with the optional CoPd layer 262 of the current polarizing structure 260 being adjacent to the top electrode layer 204.

The aforedescribed arrangement and composition of the spin transfer torque MTJ 200 may enable perpendicular anisotropy of the magnetic laminated free layer 240, without the need to overly increase the iron content of the sublayers 242, 244, 246 or excessively decrease their thickness (to promote perpendicular anisotropy). The sublayers 242, 244, 246 may undesirably become super-paramagnetic and therefore thermally unstable if they were instead required to be excessively thin (where the memory cell size is small enough for practical use in modern data storage). Hence, the aforedescribed arrangement and composition of the spin transfer torque MTJ 200 may beneficially enable perpendicular anisotropy with thicker free layer laminates, and thereby increase switching speed and/or reduce the risk of thermal instability.

The aforedescribed sequence and order of deposition of the layers of the spin transfer torque MTJ 200 is not the only possible sequence or order of deposition according to the present invention. For example, FIG. 3 is a cross-sectional diagram of a spin transfer torque MTJ 300 according to certain alternative embodiments of the present invention that have a different sequence or order of layer deposition.

The spin transfer torque MTJ 300 of FIG. 3 includes an electrically conductive base electrode layer 302 defining a substrate plane 303. In certain embodiments, the spin transfer torque MTJ 300 may be fabricated on an electrically conductive substrate, with a remaining portion of the electrically conductive substrate serving as the electrically conductive base electrode layer 302. In certain alternative embodiments, base electrode layer 302 may be fabricated as a metal layer (e.g. NiCr) deposited on a substrate (non-conductive, semi-conductive, or electrically conductive) that might be partially or wholly removed (e.g. by a conventional etching process).

In the embodiment of FIG. 3, a current polarizing structure 360 is disposed on the base electrode layer 302. The current polarizing structure 360 may include a CoFeB polarizing layer 364 having a thickness greater than 20 Angstroms, and may optionally include a CoPd layer 362. In the embodiment of FIG. 3, each of the arrows 363, 365 depicts a remnant magnetic field direction in the CoPd layer 362 and the CoFeB polarizing layer 364, respectively. As depicted by the arrows 363, 365, the CoPd layer 362 and the CoFeB polarizing layer 364 have magnetic anisotropy that is parallel to the substrate plane 303.

In the embodiment of FIG. 3, a laminated magnetic free layer 340 is disposed on the current polarizing structure 360. In certain embodiments, the laminated magnetic free layer 340 may include at least three sublayers 342, 344, 346, each one being separated from an adjacent one by a non-magnetic metallic dusting layer. For example, in the embodiment of FIG. 3, the sublayer 342 is separated from the sublayer 344

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by the non-magnetic metallic dusting layer 343, and the sublayer 344 is separated from the sublayer 346 by the non-magnetic metallic dusting layer 345. In the embodiment of FIG. 3, each of the non-magnetic metallic dusting layers 343, 345 may preferably be a tantalum dusting layer having a thickness in the range of 1 Angstroms to 7 Angstroms.

In the embodiment of FIG. 3, each of the sub-layers 342 and 346 of the laminated magnetic free layer 340 may preferably be a CoFeB sublayer having a thickness in the range of 6 Angstroms to 16 Angstroms. In certain embodiments, the sublayer 344 of the laminated magnetic free layer 340 may also be a CoFeB sublayer having a thickness in the range of 6 Angstroms to 16 Angstroms. In certain embodiments, the laminated magnetic free layer 340 preferably does not include more than four such CoFeB sublayers, each separated from an adjacent one by a tantalum dusting layer. However, in certain alternative embodiments, the sublayer 344 of the laminated magnetic free layer 340 may preferably comprise CoPt, FePt, or CoPd, and have a thickness in the range of 10 Angstroms to 30 Angstroms.

In the embodiment of FIG. 3, each of the arrows 352, 354, 356 depicts a remnant magnetic field direction in a corresponding sublayer 342, 344, 346 of the laminated magnetic free layer 340, respectively. The arrows 352, 354, 356 are shown as double-headed arrows as an indication that the laminated free layer 340 is intended to have a magnetization that is programmable (by the passage of a polarized current) to be oriented vertically up or down in the view of FIG. 3. The arrows 352, 354, 356 are also drawn so as to indicate that the magnetic anisotropy of each of the sublayers 342, 344, 346 of the laminated magnetic free layer 340 is preferably oriented perpendicular to the substrate plane 303.

The presently disclosed structure and composition of the laminated free layer 340 of the embodiment of FIG. 3, and its anisotropy perpendicular to the substrate plane 303, may beneficially reduce the programming current required to change the magnetic orientation of the laminated free layer 340. By contrast, the required programming current may be undesirably higher if the sublayers 342, 344, 346 of the laminated free layer 340 instead comprised FePt and/or had anisotropy parallel to the substrate plane 303. Moreover, the presently disclosed structure and composition of the laminated free layer 340 of the embodiment of FIG. 3 may allow deposition at lower temperature, simplifying the manufacturing process and reducing the risk of thermal degradation to the fabricated spin transfer torque MTJ 300 and its tunneling magneto resistive (TMR) performance.

In the embodiment of FIG. 3, an insulative barrier layer 330 is disposed on the laminated magnetic free layer 340, so that the sublayer 346 is disposed adjacent to the insulative barrier layer 330. In certain embodiments, the insulative barrier layer 330 may preferably comprise MgO having a thickness in the range of 8 Angstroms to 20 Angstroms, which in certain embodiments may provide a resistance area product (“RA”) in the range 1 to 6 $\Omega\cdot\mu\text{m}^2$.

In certain embodiments, the current polarizing structure 360 is preferably spaced from the laminated magnetic free layer 340 by a MgO spacer layer 366 that is adjacent to the laminated magnetic free layer 340. In such embodiments, the MgO spacer layer 366 preferably has a thickness in the range of 2 to 8 Angstroms, which may provide a resistance area product (“RA”) in the range 0.2 to 0.8 $\Omega\cdot\mu\text{m}^2$ —preferably substantially less than that of the insulative barrier layer 330.

In the embodiment of FIG. 3, a magnetic reference layer structure 310 is disposed on the insulative barrier layer 330. The magnetic reference layer structure 310 may include

various sub-layers. For example, the magnetic reference layer structure **310** may include a pinned layer **312**, for example comprising CoFeB. In the embodiment of FIG. 3, the pinned layer **312** is disposed adjacent to the insulative barrier layer **330**.

The magnetic reference layer structure **310** may also include a pair of antiferromagnetically coupled pinning layers **314**, **316** separated by a thin non-magnetic dusting layer **315** (e.g. ruthenium). The magnetic reference layer structure **310** may optionally further include an outer layer **318** (optionally comprising an alloy of manganese, such as PtMn, IrMn, NiMn, FeMn).

In FIG. 3, the arrow **322** depicts a remnant magnetic field direction in the pinned layer **312**, which corresponds to a magnetic anisotropy in the pinned layer **312** that is perpendicular to the substrate plane **303**. The arrows **324**, **326** depict the remnant magnetic field directions in the pinning layers **314**, **316**, respectively, each corresponding to a magnetic anisotropy that is perpendicular to the substrate plane **303**.

In the embodiment of FIG. 3, the primary function of the reference layer structure **310** is to maintain the magnetic orientation **322** of the pinned layer **312** in a fixed (i.e. "pinned") orientation, despite magnetic torques that may be applied to the pinned layer **312** by spin polarized electrical currents passing through the spin transfer torque MTJ **300** for programming or sensing, and regardless of external magnetic fields that the spin transfer torque MTJ **300** might experience from its environment. The pinned layer **312** may be separated from the antiferromagnetically coupled pinning layers **314**, **316**, by a thin non-magnetic metallic layer **313** (e.g. tantalum).

In the embodiment of FIG. 3, the spin transfer torque MTJ **300** further includes an electrically conductive top electrode layer **304** that is disposed on the reference layer structure **310**, with the outer layer **318** of the reference layer structure **310** being adjacent to the top electrode layer **304**.

The aforescribed arrangement and composition of the spin transfer torque MTJ **300** may enable perpendicular anisotropy of the magnetic laminated free layer **340**, without the need to overly increase the iron content of the sublayers **342**, **344**, **346** or excessively decrease their thickness (to promote perpendicular anisotropy). The sublayers **342**, **344**, **346** may undesirably become super-paramagnetic and therefore thermally unstable if they were instead required to be excessively thin (where the memory cell size is small enough for practical use in modern data storage). Hence, the aforescribed arrangement and composition of the spin transfer torque MTJ **300** may beneficially enable perpendicular anisotropy with thicker free layer laminates, and thereby increase switching speed and/or reduce the risk of thermal instability.

In the foregoing specification, the invention is described with reference to specific exemplary embodiments, but those skilled in the art will recognize that the invention is not limited to those. It is contemplated that various features and aspects of the invention may be used individually or jointly and possibly in a different environment or application. The specification and drawings are, accordingly, to be regarded as illustrative and exemplary rather than restrictive. For example, the word "preferably," and the phrase "preferably but not necessarily," are used synonymously herein to consistently include the meaning of "not necessarily" or optionally. The drawings are not necessarily to scale. "Comprising," "including," and "having," are intended to be open-ended terms.

What is claimed is:

1. A spin transfer torque magnetic junction comprising:
 - an electrically conductive base electrode layer defining a substrate plane;
 - a magnetic reference layer structure disposed on the base electrode layer and having magnetic anisotropy perpendicular to the substrate plane;
 - an insulative barrier layer disposed on the magnetic reference layer structure;
 - a laminated magnetic free layer disposed on the insulative barrier layer and having magnetic anisotropy perpendicular to the substrate plane;
 - a current polarizing structure disposed on the laminated magnetic free layer and having magnetic anisotropy parallel to the substrate plane; and
 - an electrically conductive top electrode layer disposed on the current polarizing structure;
 wherein the laminated magnetic free layer comprises at least three sublayers of CoFeB, each being separated from an adjacent CoFeB sublayer by one of a plurality of dusting layers.
2. The spin transfer torque magnetic junction of claim 1 wherein the laminated magnetic free layer comprises no more than four sublayers of CoFeB.
3. The spin transfer torque magnetic junction of claim 1 wherein each of the plurality of dusting layers comprises tantalum with a thickness in the range of 1 Angstroms to 7 Angstroms.
4. The spin transfer torque magnetic junction of claim 1 wherein the current polarizing structure comprises a CoPd layer that is adjacent to the top electrode layer, and a MgO spacer layer that is adjacent to the laminated magnetic free layer.
5. The spin transfer torque magnetic junction of claim 1 wherein the magnetic reference layer structure comprises a pinned layer comprising CoFeB that is disposed adjacent to the insulative barrier layer, and a pair of antiferromagnetically coupled pinning layers, each having magnetic anisotropy perpendicular to the substrate plane.
6. The spin transfer torque magnetic junction of claim 5 wherein the magnetic reference layer structure further comprises an outer layer comprising an alloy of manganese that is disposed adjacent to the base electrode layer.
7. The spin transfer torque magnetic junction of claim 1 wherein the insulative barrier layer comprises MgO having a thickness in the range of 8 Angstroms to 20 Angstroms.
8. A memory device comprising the spin transfer torque magnetic junction of claim 1.
9. A spin transfer torque magnetic junction comprising:
 - an electrically conductive base electrode layer defining a substrate plane;
 - a current polarizing structure disposed on the base electrode layer and having magnetic anisotropy parallel to the substrate plane;
 - a laminated magnetic free layer disposed on the current polarizing structure and having magnetic anisotropy perpendicular to the substrate plane;
 - an insulative barrier layer disposed on the laminated magnetic free layer;
 - a magnetic reference layer structure disposed on the insulative barrier layer and having magnetic anisotropy perpendicular to the substrate plane; and
 - an electrically conductive top electrode layer disposed on the magnetic reference layer structure;

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wherein the laminated magnetic free layer comprises at least three sublayers of CoFeB, each being separated from an adjacent CoFeB sublayer by one of a plurality of dusting layers.

10. The spin transfer torque magnetic junction of claim 9 wherein each of the plurality of dusting layers comprises tantalum with a thickness in the range of 1 Angstroms to 7 Angstroms.

11. The spin transfer torque magnetic junction of claim 9 wherein the current polarizing structure comprises a CoPd layer that is adjacent to the base electrode layer, a CoFeB polarizing layer, and a MgO spacer layer that is adjacent to the laminated magnetic free layer.

12. The spin transfer torque magnetic junction of claim 9 wherein the magnetic reference layer structure comprises a pinned layer comprising CoFeB that is disposed adjacent the insulative barrier layer, and a pair of antiferromagnetically coupled pinning layers, each having magnetic anisotropy perpendicular to the substrate plane.

13. The spin transfer torque magnetic junction of claim 12 wherein the magnetic reference layer structure further comprises an outer layer comprising an alloy of manganese that is disposed adjacent to the top electrode layer.

14. The spin transfer torque magnetic junction of claim 12 wherein the insulative barrier layer comprises MgO having a thickness in the range of 8 Angstroms to 20 Angstroms.

15. The spin transfer torque magnetic junction of claim 12 wherein the laminated magnetic free layer comprises no more than four sublayers of CoFeB.

16. A memory device comprising the spin transfer torque magnetic junction of claim 9.

17. A spin transfer torque magnetic junction comprising: an electrically conductive base electrode layer defining a substrate plane;

a magnetic reference layer structure disposed on the base electrode layer and having magnetic anisotropy perpendicular to the substrate plane;

an insulative barrier layer disposed on the magnetic reference layer;

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a laminated magnetic free layer disposed on the insulative barrier layer and having magnetic anisotropy perpendicular to the substrate plane;

a current polarizing structure disposed on the laminated magnetic free layer and having magnetic anisotropy parallel to the substrate plane; and

an electrically conductive top electrode layer disposed on the current polarizing structure;

wherein the laminated magnetic free layer comprises first, second, and third sublayers, each comprising a ferromagnetic material selected from the group consisting of CoFeB, CoPt, FePt, and CoPd; and

wherein the first and second sublayers are separated by a first dusting layer, and the second and third sublayers are separated by a second dusting layer.

18. The spin transfer torque magnetic junction of claim 17 wherein each of the first and second dusting layers comprises tantalum with a thickness in the range of 1 Angstroms to 7 Angstroms.

19. The spin transfer torque magnetic junction of claim 17 wherein the current polarizing structure comprises a CoPd layer that is adjacent to the top electrode layer, a CoFeB polarizing layer, and a MgO spacer layer that is adjacent to the laminated magnetic free layer.

20. The spin transfer torque magnetic junction of claim 17 wherein the magnetic reference layer structure comprises a pinned layer comprising CoFeB that is disposed adjacent the insulative barrier layer, and a pair of antiferromagnetically coupled pinning layers, each having magnetic anisotropy perpendicular to the substrate plane.

21. The spin transfer torque magnetic junction of claim 20 wherein the magnetic reference layer structure further comprises an outer layer comprising an alloy of manganese that is disposed adjacent to the base electrode layer.

22. The spin transfer torque magnetic junction of claim 17 wherein the insulative barrier layer comprises MgO having a thickness in the range of 8 Angstroms to 20 Angstroms.

23. A memory device comprising the spin transfer torque magnetic junction of claim 17.

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